



UMZ1N DUAL TRANSISTOR (NPN+PNP)

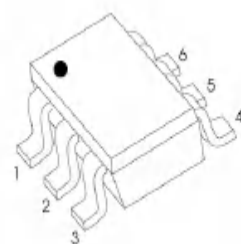
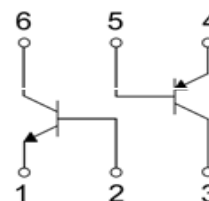
DESCRIPTION

Silicon epitaxial planar transistor

FEATURES

- 2SA1037AK and 2SC2412K are housed independently in a package
- Transistor elements independent, eliminating interference
- Mounting cost and area can be cut in half

MARKING: Z1



SOT-363

TR1 MAXIMUM RATINGS $T_a=25^{\circ}\text{C}$ unless otherwise noted

Symbol	Parameter	Value	Unit
V_{CBO}	Collector- Base Voltage	60	V
V_{CEO}	Collector-Emitter Voltage	50	V
V_{EBO}	Emitter-Base Voltage	7	V
I_{C}	Collector Current -Continuous	0.15	A
P_{C}	Collector Power Dissipation	0.15	W
T_{J}	Junction Temperature	150	$^{\circ}\text{C}$
T_{stg}	Storage Temperature	-55-150	$^{\circ}\text{C}$

TR2 MAXIMUM RATINGS $T_a=25^{\circ}\text{C}$ unless otherwise noted

Symbol	Parameter	Value	Unit
V_{CBO}	Collector- Base Voltage	-60	V
V_{CEO}	Collector-Emitter Voltage	-50	V
V_{EBO}	Emitter-Base Voltage	-6	V
I_{C}	Collector Current -Continuous	-0.15	A
P_{C}	Collector Power Dissipation	0.15	W
T_{J}	Junction Temperature	150	$^{\circ}\text{C}$
T_{stg}	Storage Temperature	-55-150	$^{\circ}\text{C}$



TR1 NPN ELECTRICAL CHARACTERISTICS (Ta=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=50\mu A, I_E=0$	60			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=1mA, I_B=0$	50			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=50\mu A, I_C=0$	7			V
Collector cut-off current	I_{CBO}	$V_{CB}=60V, I_E=0$			0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=7V, I_C=0$			0.1	μA
DC current gain	h_{FE}	$V_{CE}=6V, I_C=1mA$	120		560	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=50mA, I_B=5mA$			0.4	V
Transition frequency	f_T	$V_{CE}=12V, I_C=2mA, f=100MHz$		180		MHz
Collector output capacitance	C_{ob}	$V_{CB}=12V, I_E=0, f=1MHz$		2.0	3.5	pF

TR1 PNP ELECTRICAL CHARACTERISTICS (Ta=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=-50\mu A, I_E=0$	-60			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=-1mA, I_B=0$	-50			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=-50\mu A, I_C=0$	-6			V
Collector cut-off current	I_{CBO}	$V_{CB}=-60V, I_E=0$			-0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=-6V, I_C=0$			-0.1	μA
DC current gain	h_{FE}	$V_{CE}=-6V, I_C=-1mA$	120		560	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=-50mA, I_B=-5mA$			-0.5	V
Transition frequency	f_T	$V_{CE}=-12V, I_C=-2mA, f=100MHz$		140		MHz
Collector output capacitance	C_{ob}	$V_{CB}=-12V, I_E=0, f=1MHz$			5	pF

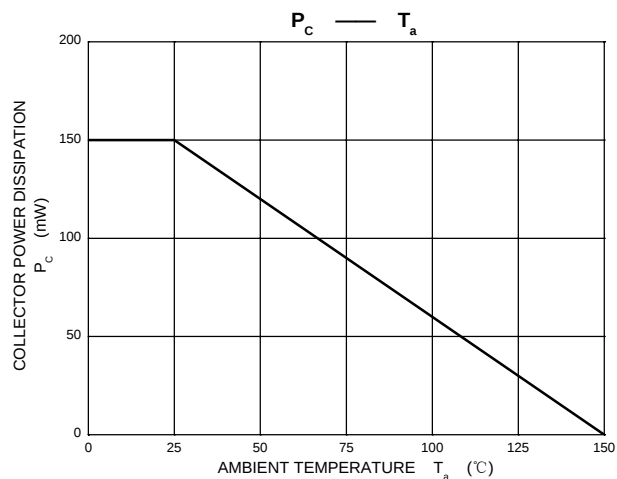
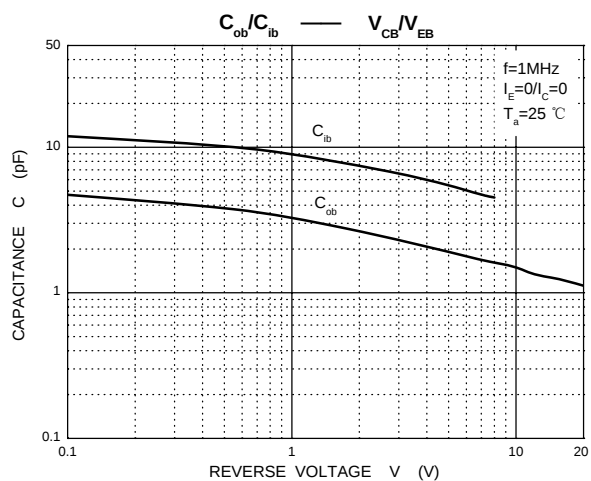
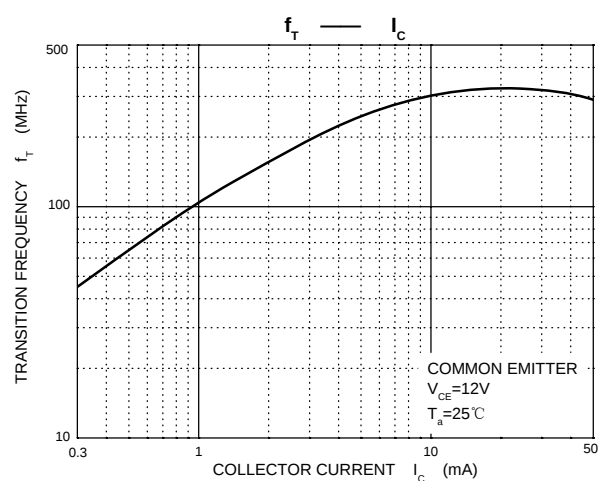
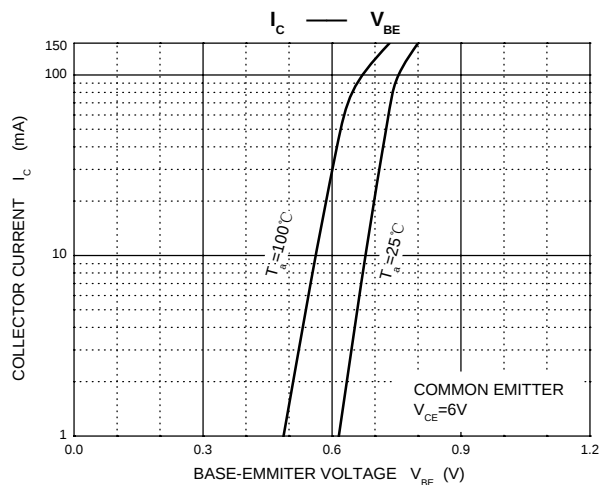
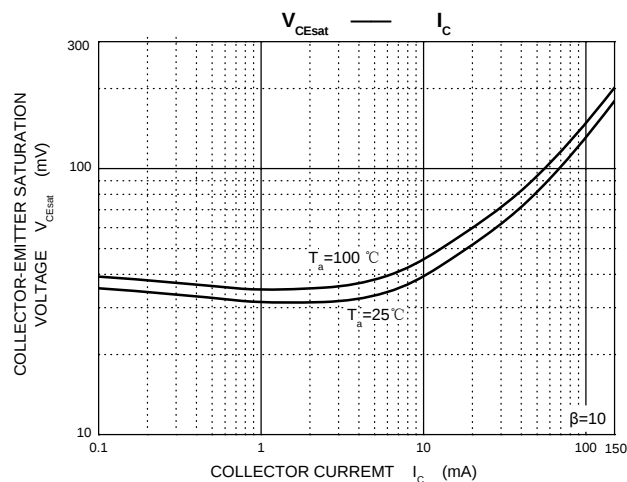
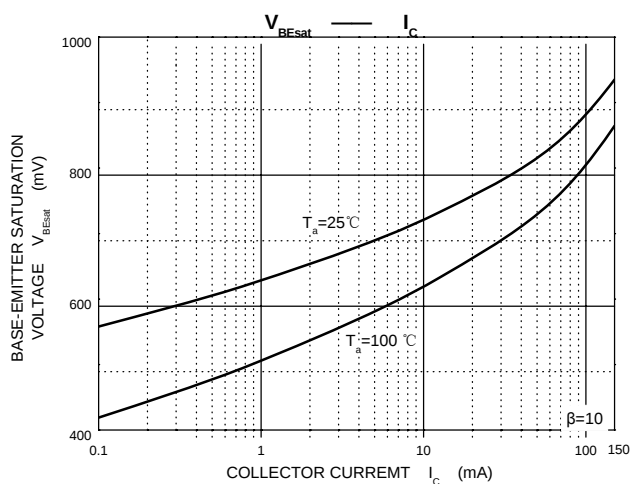
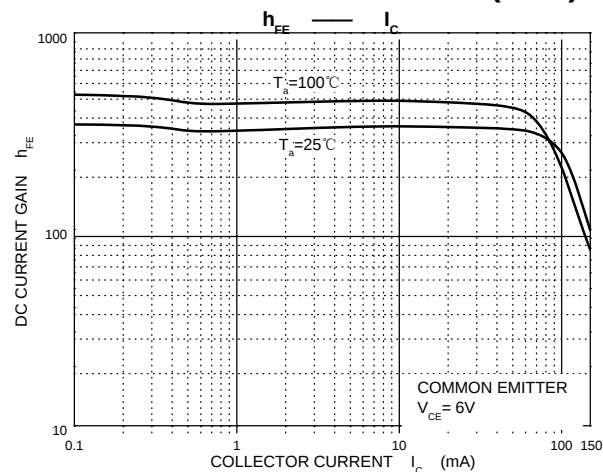
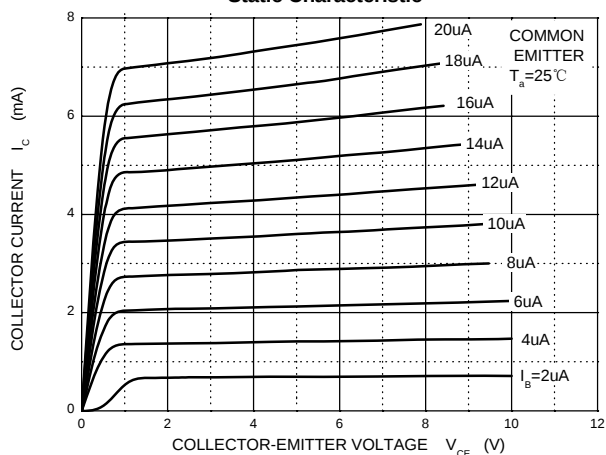


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MAITUO ELECTRONIC

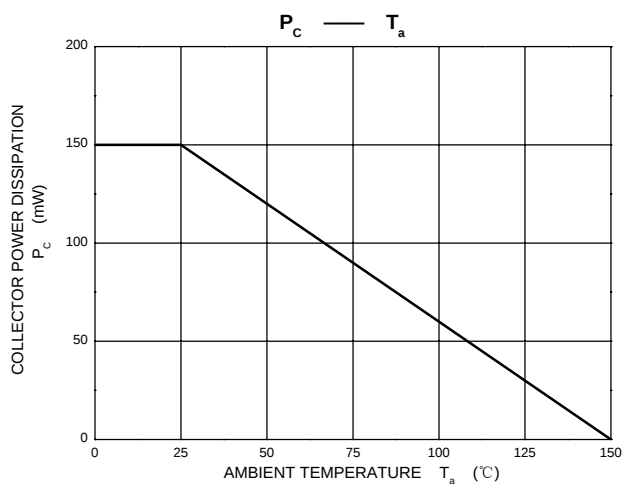
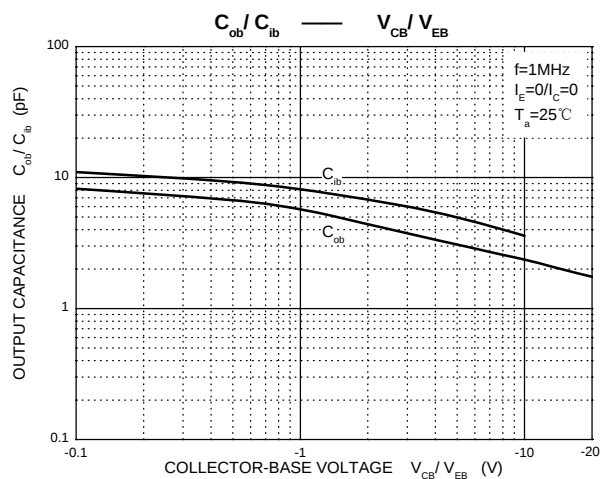
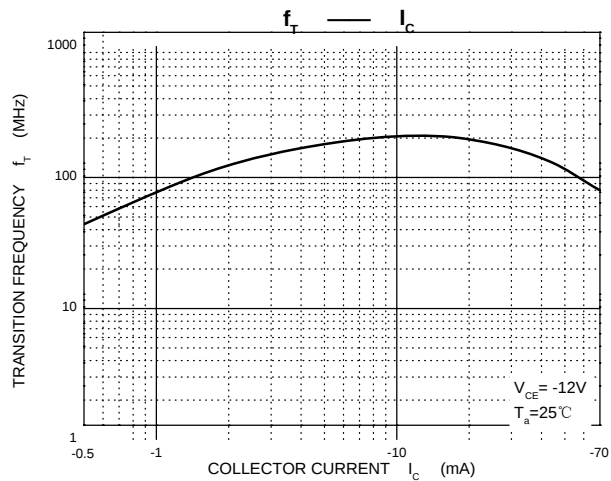
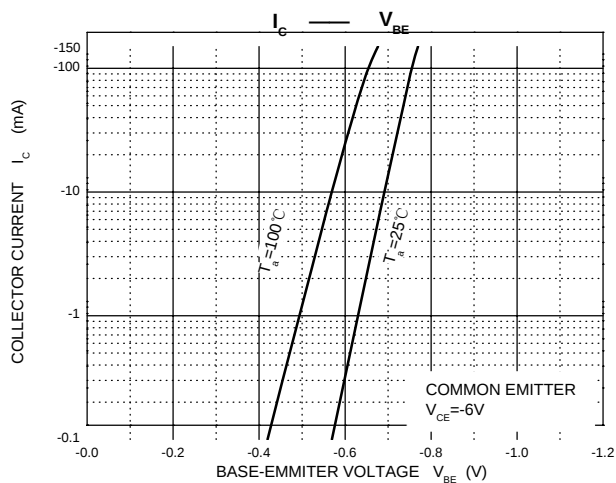
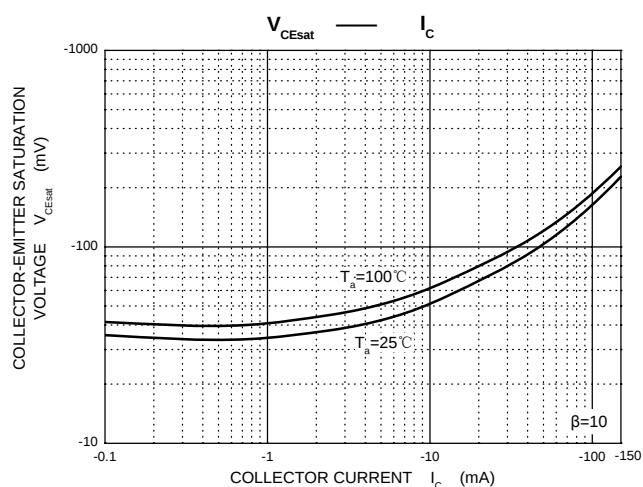
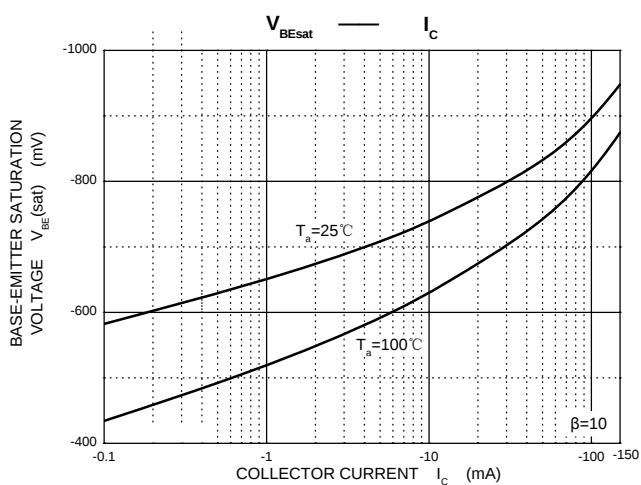
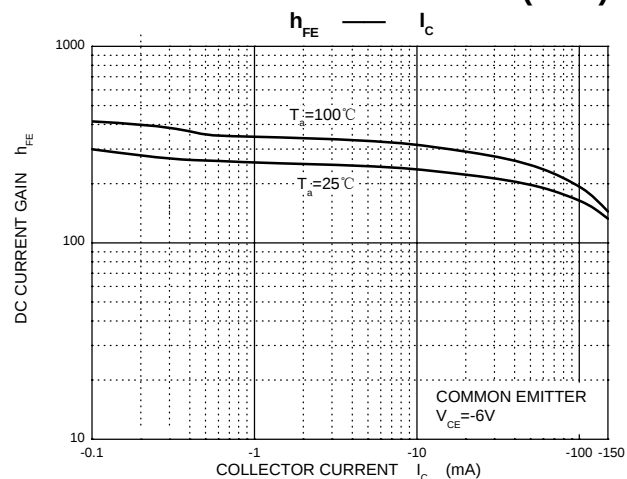
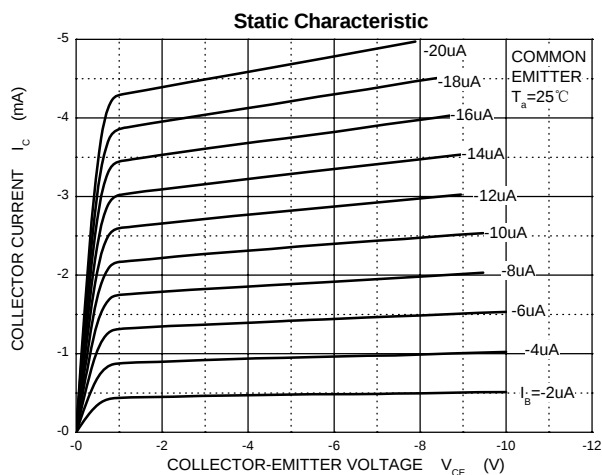
(NPN)

Static Characteristic



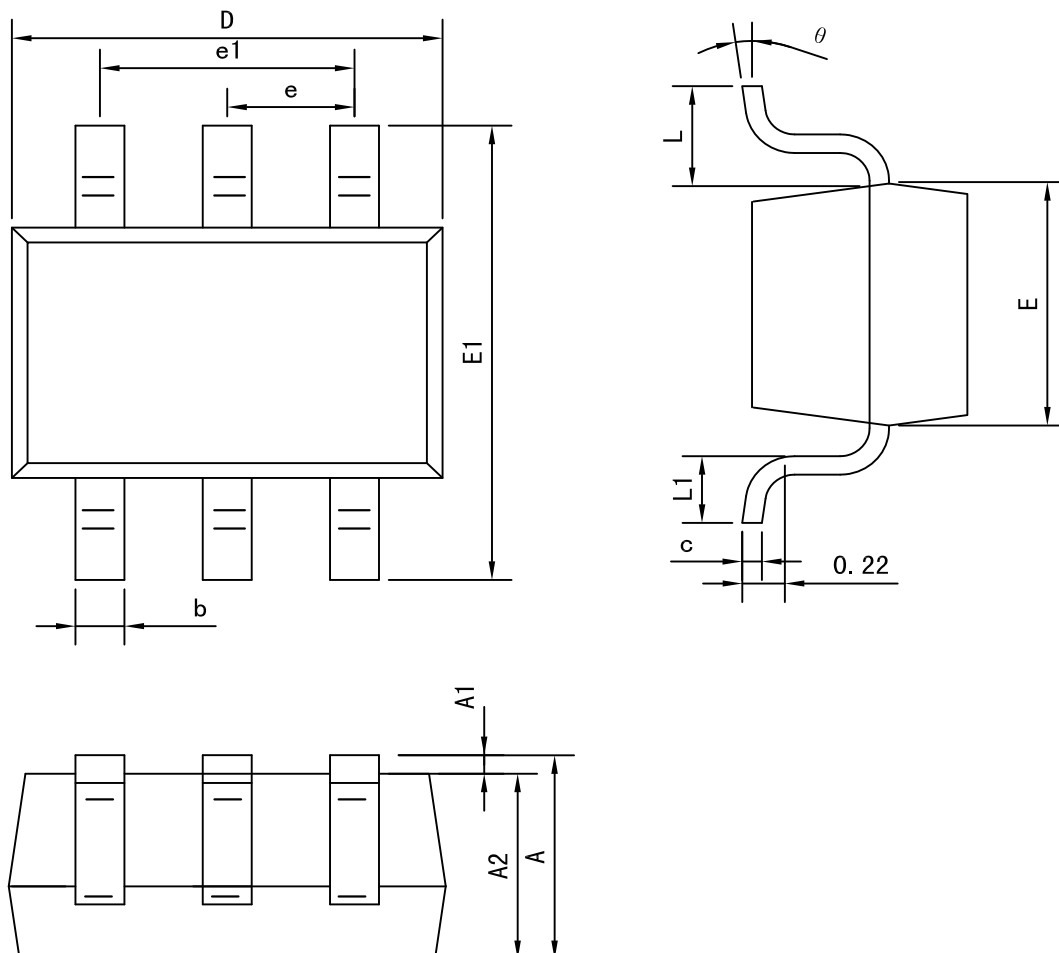


(PNP)





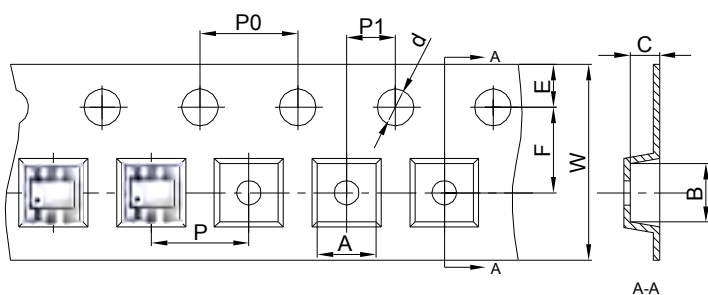
SOT-363 Package outline dimensions



Symbol	Dimension in Millimeters	
	Min	Max
A	0.900	1.100
A1	0.000	0.100
A2	0.900	1.000
b	0.150	0.350
c	0.080	0.150
D	2.000	2.200
E	1.150	1.350
E1	2.150	2.450
e	0.650 TYP	
e1	1.200	1.400
L	0.525 REF	
L1	0.260	0.460
θ	0°	8°



SOT-363 Embossed Carrier Tape



Packaging Description:

SOT-363 parts are shipped in tape. The carrier tape is made from a dissipative (carbon filled) polycarbonate resin. The cover tape is a multilayer film (Heat Activated Adhesive in nature) primarily composed of polyester film, adhesive layer, sealant, and anti-static sprayed agent. These reeled parts in standard option are shipped with 3,000 units per 7" or 17.8cm diameter reel. The reels are clear in color and is made of polystyrene plastic (anti-static coated).

Dimensions are in millimeter											
Pkg type	A	B	C	d	E	F	P0	P	P1	W	
SOT-363	2.25	2.55	1.20	Ø1.50	1.75	3.50	4.00	4.00	2.00	8.00	

SOT-363 Tape Leader and Trailer

